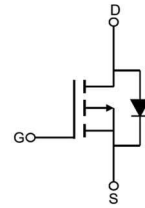


AP20P30S

P-Channel Enhancement Mosfet

Feature

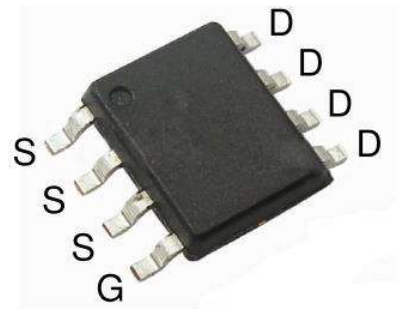
- -30V,-15A
 $R_{DS(ON)} < 8.4m\Omega @ V_{GS} = -10V$ TYP:6.8 m Ω
 $R_{DS(ON)} < 12m\Omega @ V_{GS} = -4.5V$ TYP:10 m Ω
- Trench DMOS Power MOSFET
- Fast Switching
- Exceptional on-resistance and maximum DC current capability



Schematic diagram

Application

- DC/DC Converter
- Load Switch for Portable Devices
- Battery Switch



SOP-8

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity (PCS)
20P30S	AP20P30S	SOP-8	13 inch	-	4000

ABSOLUTE MAXIMUM RATINGS ($T_a=25^{\circ}C$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	-30	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current ($T_a=25^{\circ}C$)	I_D	-15	A
Continuous Drain Current ($T_a=100^{\circ}C$)	I_D	-10.5	A
Pulsed Drain Current ⁽¹⁾	I_{DM}	-60	A
Singel Pulsed Avalanche Energy ⁽⁴⁾	E_{AS}	156	mJ
Power Dissipation	P_D	3.7	W
Thermal Resistance from Junction to Ambient	$R_{\theta JA}$	42.8	$^{\circ}C/W$
Junction Temperature	T_J	150	$^{\circ}C$
Storage Temperature	T_{STG}	-55~ +150	$^{\circ}C$

MOSFET ELECTRICAL CHARACTERISTICS(T_a=25°C unless otherwise noted)

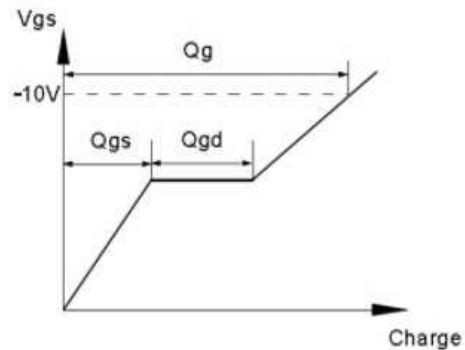
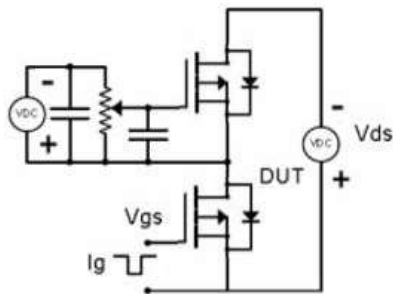
Parameter	Symbol	Test Condition	Min	Type	Max	Unit
Static Characteristics						
Drain-source breakdown voltage	V _{(BR)DSS}	V _{GS} = 0V, I _D = -250μA	-30	-	-	V
Zero gate voltage drain current	I _{DSS}	V _{DS} = -30V, V _{GS} = 0V	-	-	-1	μA
Gate-body leakage current	I _{GSS}	V _{GS} = ±20V, V _{DS} = 0V	-	-	±100	nA
Gate threshold voltage ⁽²⁾	V _{GS(th)}	V _{DS} = V _{GS} , I _D = -250μA	-1	-1.5	-2.5	V
Drain-source on-resistance ⁽²⁾	R _{DS(on)}	V _{GS} = -10V, I _D = -10A	-	6.8	8.4	mΩ
		V _{GS} = -4.5V, I _D = -5A	-	10	12	
Dynamic characteristics						
Input Capacitance	C _{iss}	V _{DS} = -15V, V _{GS} = 0V, f = 1MHz	-	3142	-	pF
Output Capacitance	C _{oss}		-	424	-	
Reverse Transfer Capacitance	C _{rss}		-	420	-	
Switching characteristics						
Turn-on delay time	t _{d(on)}	V _{DD} = -15V, I _D = -15A V _{GS} = -10V, R _G = 2.5Ω	-	13	-	ns
Turn-on rise time	t _r		-	47	-	
Turn-off delay time	t _{d(off)}		-	99	-	
Turn-off fall time	t _f		-	22	-	
Total Gate Charge	Q _g	V _{DS} = -15V, I _D = -15A, V _{GS} = -10V	-	65	-	nC
Gate-Source Charge	Q _{gs}		-	9	-	
Gate-Drain Charge	Q _{gd}		-	15	-	
Source-Drain Diode characteristics						
Diode Forward voltage ⁽²⁾	V _{DS}	V _{GS} = 0V, I _S = -15A	-	-	-1.2	V
Diode Forward current ⁽³⁾	I _S		-	-	-15	A

Notes:

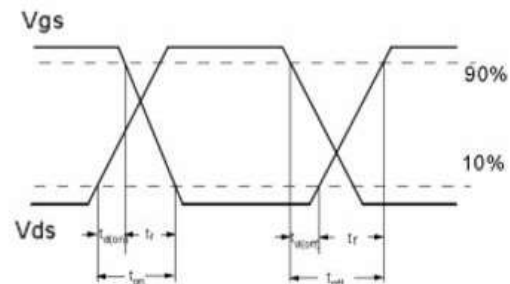
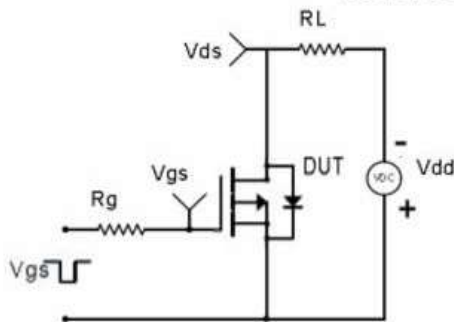
1. Repetitive Rating: pulse width limited by maximum junction temperature
2. Pulse Test: pulse width ≤ 300μs, duty cycle ≤ 2%
3. Surface Mounted on FR4 Board, t ≤ 10 sec
4. L = 0.5mH, V_{DD} = -15V, R_G = 25Ω, T_J = 25°C

Test Circuit & Waveform

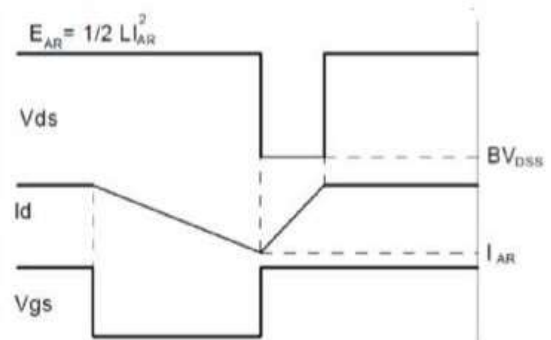
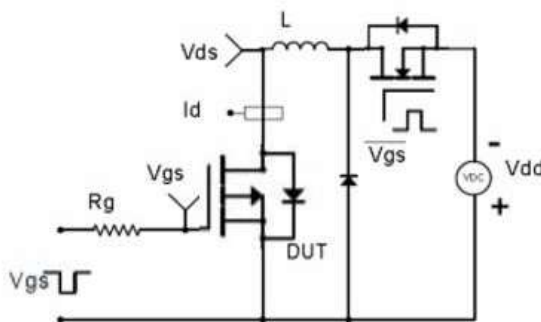
Gate Charge Test Circuit & Waveform



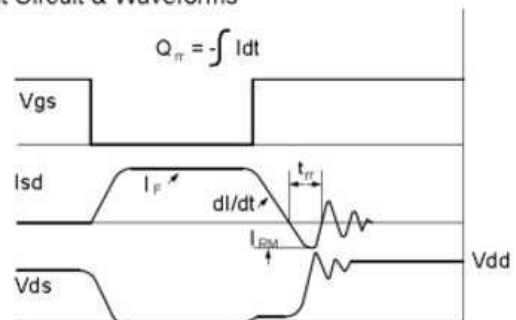
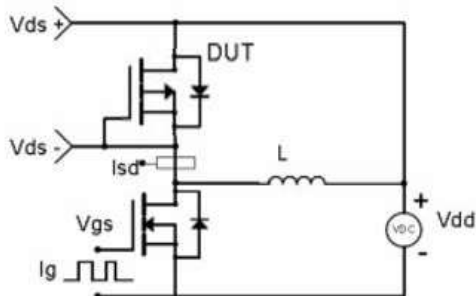
Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms



Typical Performance Characteristics

Fig.1 Power Dissipation Derating Curve

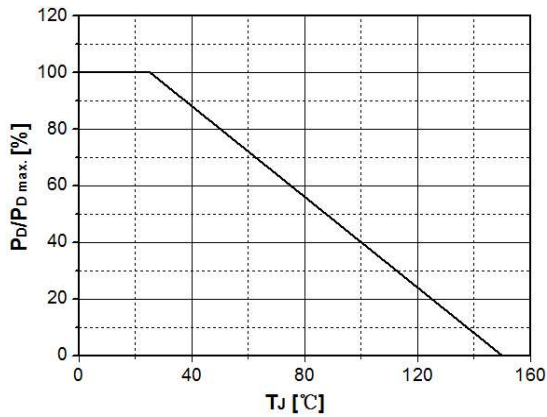


Fig.2 Avalanche Energy Derating Curve vs. Junction Temperature

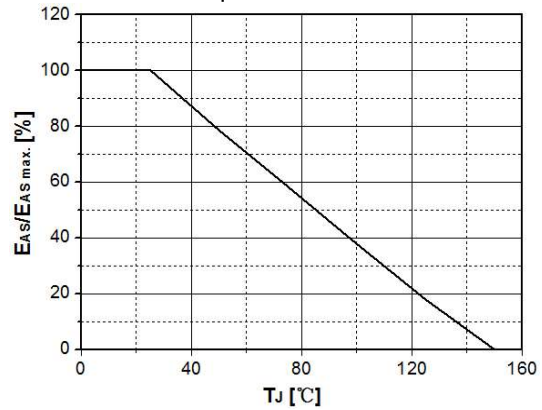


Fig.3 Typical Output Characteristics

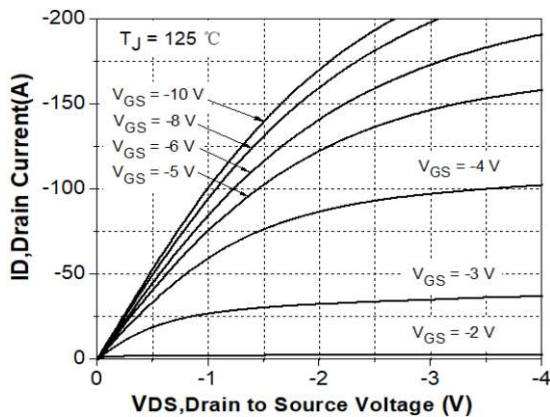


Fig. 4 Transconductance vs. Drain Current

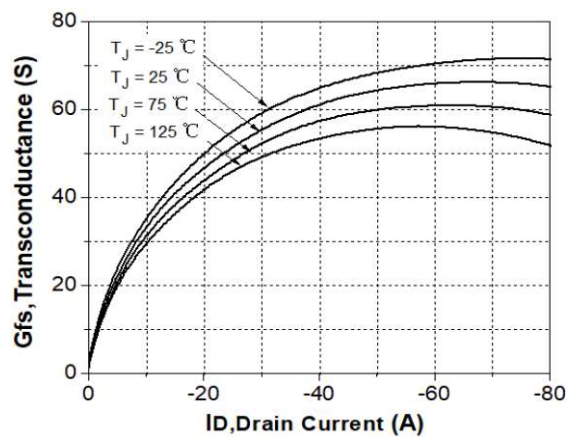


Fig.5 Typical Transfer Characteristics

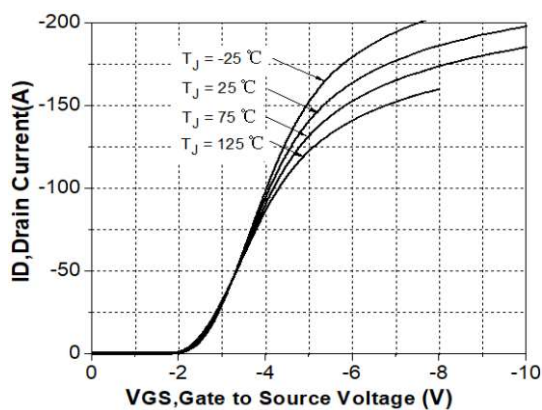


Fig. 6 State Resistance vs. Drain Current @-25°C

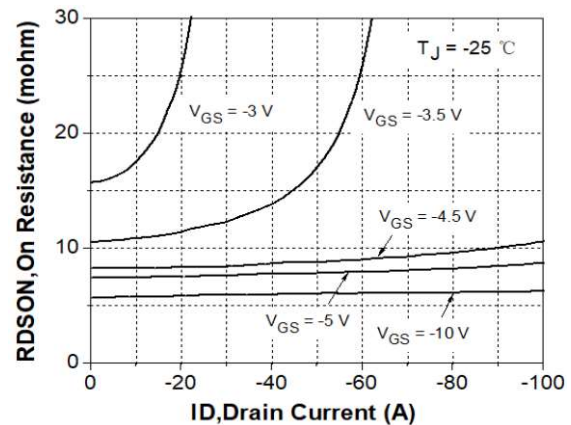


Fig.7 State Resistance vs. Drain Current @25°C

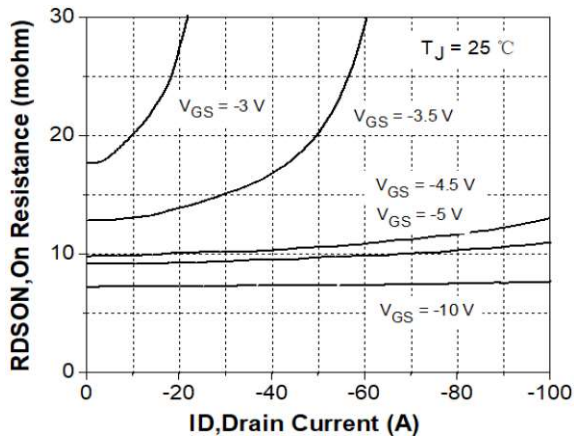


Fig. 8 State Resistance vs. Drain Current @125°C

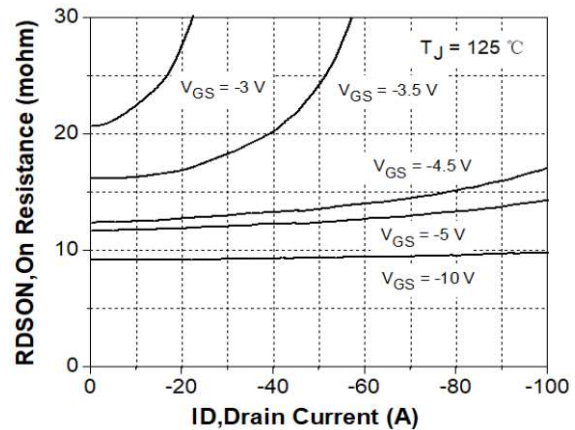


Fig.9 Typical Capacitance vs. Drain Source Voltage

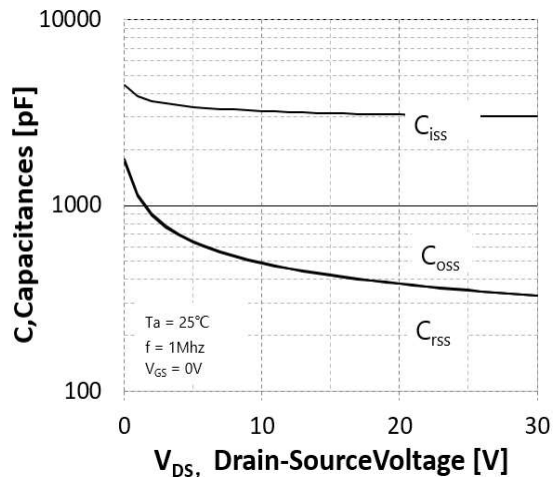


Fig.10 Dynamic Input Characteristics

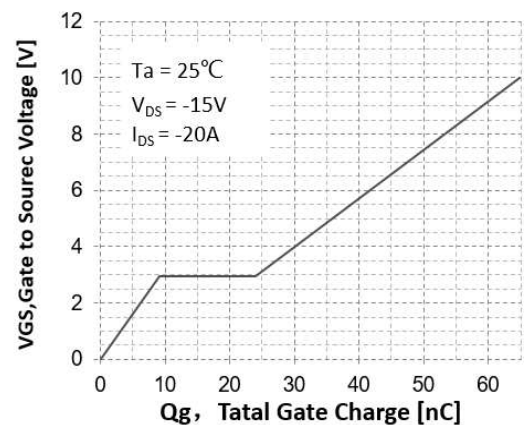


Fig.11 Breakdown Voltage vs. Junction Temperature

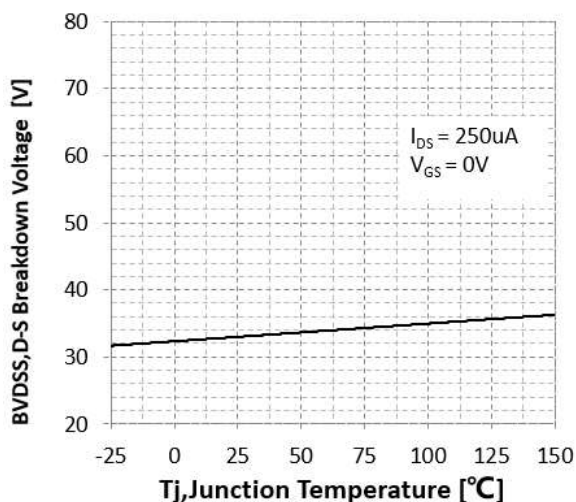


Fig. 12 Gate Threshold Voltage vs. Junction Temperature

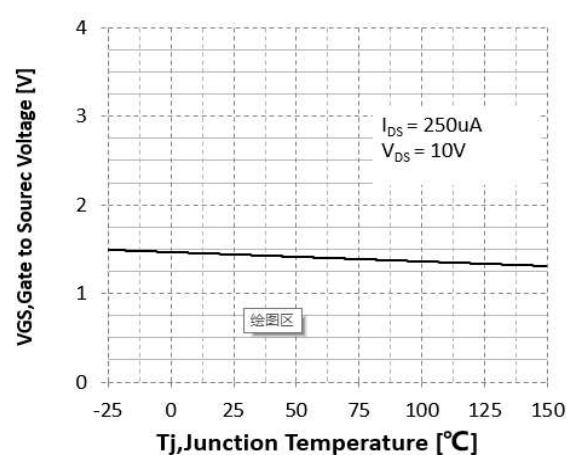


Fig.13 On-Resistance Variation vs. Junction Temperature

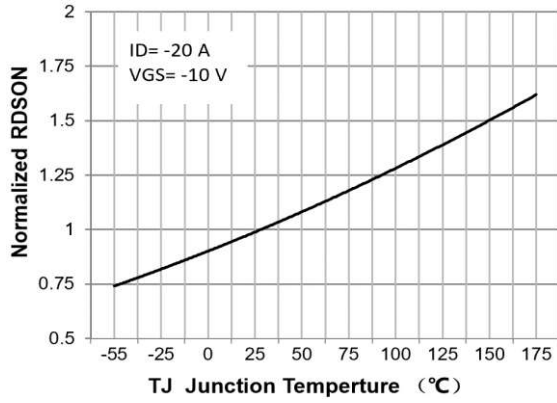


Fig.14 Maximum Drain Current vs. Case Temperature

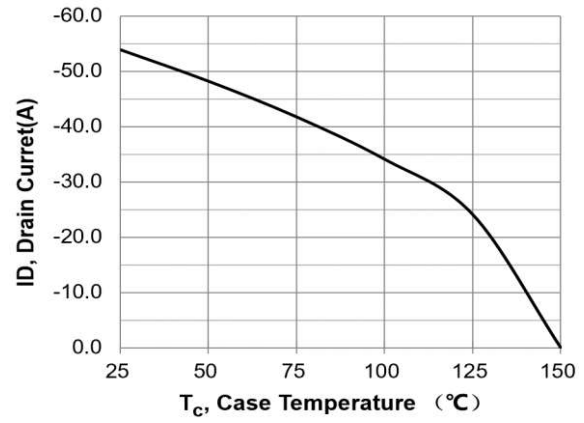


Fig.15 Body Diode Forward Voltage Vs Reverse Drain Current

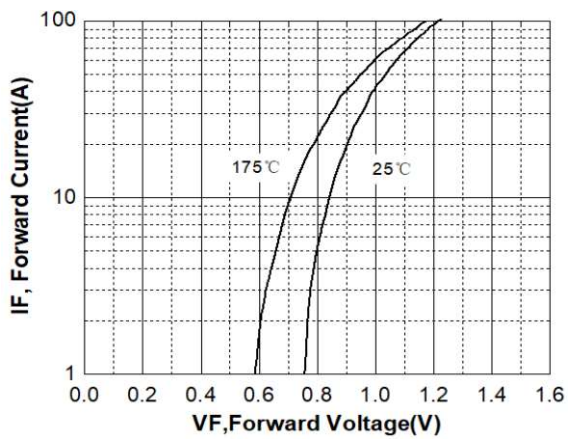


Fig.16 Safe Operating Area

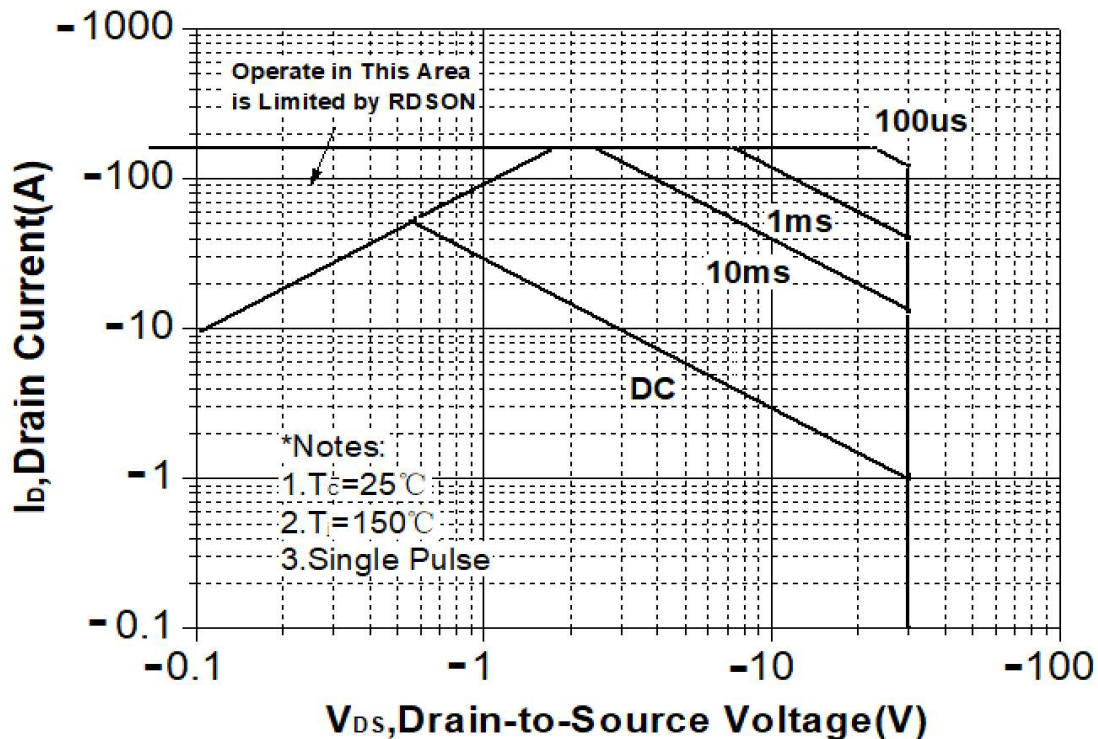
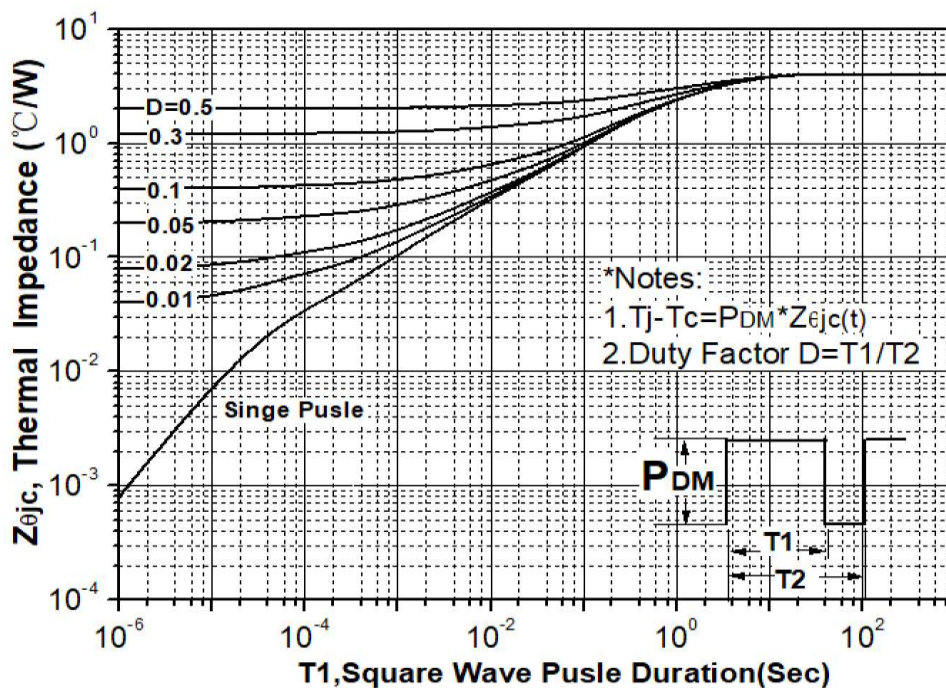


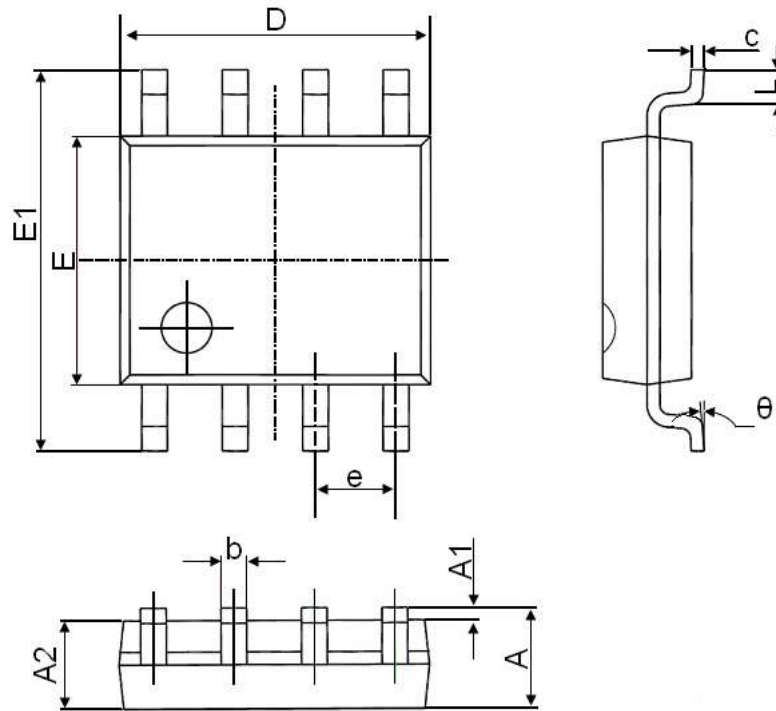
Fig. 17 Transient Thermal Response Curve



AP20P30S

P-Channel Enhancement Mosfet

SOP-8 Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	1.350	1.750	0.053	0.069
A1	0.100	0.250	0.004	0.010
A2	1.350	1.550	0.053	0.061
b	0.330	0.510	0.013	0.020
c	0.170	0.250	0.006	0.010
D	4.700	5.100	0.185	0.200
E	3.800	4.000	0.150	0.157
E1	5.800	6.200	0.228	0.244
e	1.270(BSC)		0.050(BSC)	
L	0.400	1.270	0.016	0.050
theta	0°	8°	0°	8°